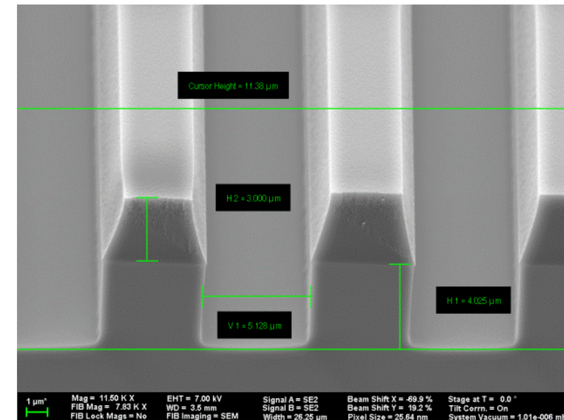
Si Shallow Trenches

Etching Mask: 3.5 um photoresist S1822

Process Condition

Parameter	Value
C4F8 (sccm)	130
SF6 (sccm)	80
Pressure (mTorr)	20
Coil Power (W)	1200
Platen Power (W)	12
Temperature (°C) (lid/wall/chuck)	40/40/21



Result

Parameter	Value
Etch Rate (µm/min)	1.0
Etch Profile	89.5°
Selectivity to Resist	>10:1